

CNZ1120

Photo Interrupter

For contactless SW, object detection

Overview

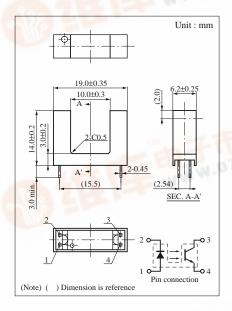
CNZ1120 is a photocoupler in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a high sensitivity phototransistor is used as the light detecting element. The two elements are arranged so as to face each other, and objects passing between them are detected.

Features

- Wide gap between emitting and detecting elements, suitable for thick plate detection Gap: 10mm
- Fast response : t_r , $t_f = 6 \mu s$ (typ.)
- The external case is molded using visible light cutoff resin. The
 case has no openings, so the photosensor is not easily susceptible
 to output attenuation resulting from dust or particles

■ Absolute Maximum Ratings (Ta = 25°C)

- F	Parameter	Symbol	Ratings	Unit
Input (Light emitting diode)	Reverse voltage (DC)	V_R	3	V
	Forward current (DC)	I_F	50	mA
	Power dissipation	P_D^{*1}	75	mW
Output (Photo transistor)	Collector current	I_{C}	20	mA
	Collector to emitter voltage	V_{CEO}	20	V
	Emitter to collector voltage	V _{ECO}	5	V
	Collector power dissipation	P _C *2	100	mW
Tomporatura	Operating ambient temperature	Topr	-5 to +60	°C
Temperature	Storage temperature	T _{stg}	-15 to +65	°C

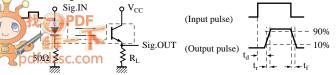


■ Electrical Characteristics (Ta = 25°C)

Parameter		Symbol	Conditions	min	typ	max	Unit
Input	Forward voltage (DC)	V _F	$I_F = 50 \text{mA}$		1.2	1.5	V
characteristics	Reverse current (DC)	I_R	$V_R = 3V$			10	μΑ
Output	Collector cutoff current	I _{CEO}	$V_{CE} = 10V, I_F = 0mA, I_D = 0mA^{*1}$			200	nA
characteristics	Collector to emitter capacitance	C_{C}	$V_{CE} = 10V$, $f = 1MHz$		5		pF
characteristics -	Collector current	I_{C}	$V_{CE} = 10V, I_F = 20mA, R_L = 100\Omega$	1.0			mA
	Response time	t_r, t_f^{*2}	$V_{CC} = 10V, I_C = 1mA, R_L = 100\Omega$		6		μs
	Collector to emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{mA}, I_C = 0.1 \text{mA}$			0.4	V

^{*1} ID: Leakage current due to scattered light

^{*2} Switching time measurement circuit



 t_d : Delay time

- t_r : Rise time (Time required for the collector current to increase from 10% to 90% of its final value)
- t_f: Fall time (Time required for the collector current to decrease from 90% to 10% of its initial value)

^{*1} Input power derating ratio is 1.0 mW/°C at Ta ≥ 25°C.

^{*2} Output power derating ratio is 1.33 mW/°C at Ta ≥ 25°C.